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6.2.4 HeteroBifunctional CrossLinking and DNA Attachment

Sommario/riassunto

Here, leading scientists report on why and how diamond can be optimized for applications in bioelectronic and electronics. They cover such topics as growth techniques, new and conventional doping mechanisms, superconductivity in diamond, and excitonic properties, while application aspects include quantum electronics at room temperature, biosensors as well as diamond nanocantilevers and SAWs.Written in a review style to make the topic accessible for a wider community of scientists working in interdisciplinary fields with backgrounds in physics, chemistry, biology and engineering, this is e